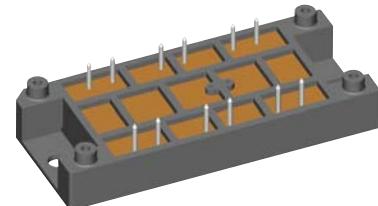
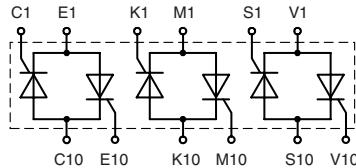


Three Phase AC Controller Modules

I_{RMS} = 3x 143 A
V_{RRM} = 800-1600 V

Preliminary data

V _{RSM} V _{DSM} V	V _{RRM} V _{DRM} V	Type
800	800	VWO 140-08io1
1200	1200	VWO 140-12io1
1400	1400	VWO 140-14io1
1600	1600	VWO 140-16io1



pin configuration see outlines

Symbol	Conditions	Maximum Ratings			Features
I _{RMS}	T _C = 85°C, 50 - 400 Hz (per phase)	101	A		• Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
I _{RMS}	T _C = 85°C, 50 - 400 Hz (per phase) for 10 sec.	143	A		• Package with DCB base plate
I _{TAVM}	T _C = 85°C; (180° sine)	46	A		• Isolation voltage 3600 V~
I _{TSM}	T _{VJ} = 45°C; V _R = 0	1150	A		• Planar passivated chips
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1240	A		• UL applied
I _{TSM}	T _{VJ} = 125°C V _R = 0	1040	A		
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1120	A		
I ² t	T _{VJ} = 45°C V _R = 0	6610	A ² s		
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	6460	A ² s		
(di/dt) _{cr}	T _{VJ} = 125°C f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.45 A di _G /dt = 0.45 A/µs	5410	A ² s		
	non repetitive, I _T = 45 A	5270	A ² s		
(dv/dt) _{cr}	T _{VJ} = 125°C; R _{GM} = ∞; method 1 (linear voltage rise)	150	A/µs		
(dv/dt) _{cr}	V _{DR} = 2/3 V _{DRM}	1000	V/µs		
P _{GM}	T _{VJ} = 125°C I _T = I _{TAVM}	10	W		
P _{GAVM}		5	W		
V _{RGM}		0.5	W		
T _{VJ}		-40...+125	°C		
T _{VJM}	for 10 sec.	150	°C		
T _{stg}		-40...+125	°C		
V _{ISOL}	50/60 Hz, RMS	t = 1 min	3000	V~	
	I _{ISOL} ≤ 1 mA	t = 1 s	3600	V~	
M _d	Mounting torque (M5)	2-2.5	Nm.		
		18-22	lb.in.		
Weight	typ.	80	g		

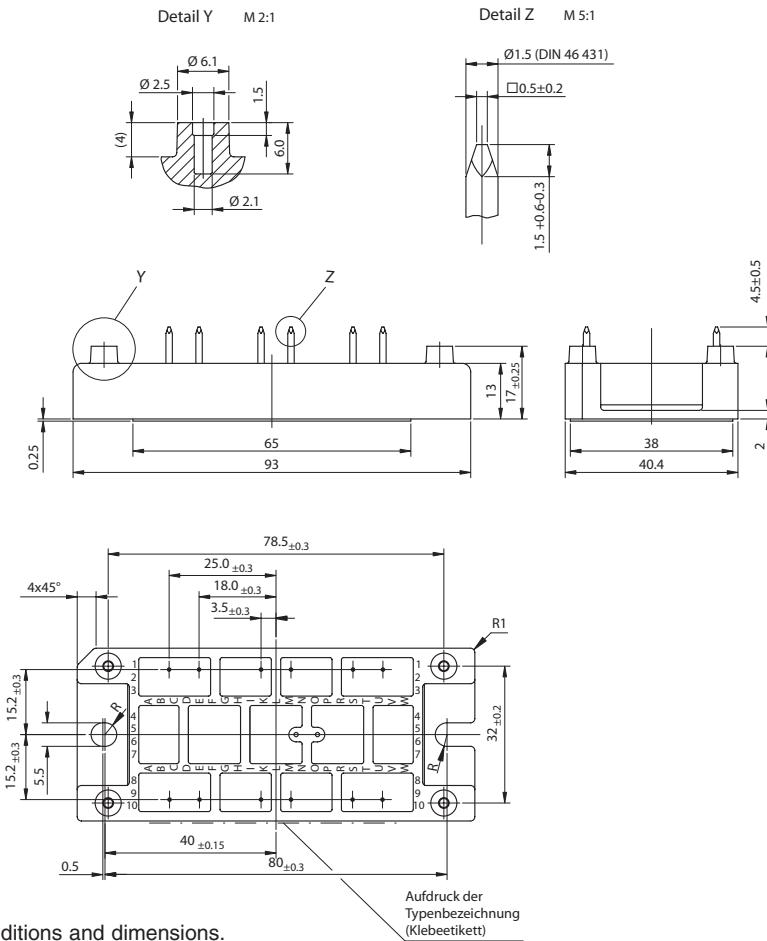
Data according to IEC 60747 refer to a single thyristor unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

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Symbol	Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = 125^\circ C; V_R = V_{RRM}; V_D = V_{DRM}$	≤	5	mA
V_T	$I_T = 140 A; T_{VJ} = 25^\circ C$	≤	1.5	V
V_{TO}	For power-loss calculations only	0.85		V
r_T		5.2		$m\Omega$
V_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$	≤	1.5	V
	$T_{VJ} = -40^\circ C$	≤	1.6	V
I_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$	≤	100	mA
	$T_{VJ} = -40^\circ C$	≤	200	mA
V_{GD}	$T_{VJ}=125^\circ C; V_D = \frac{2}{3} V_{DRM}$	≤	0.2	V
I_{GD}		≤	5	mA
I_L	$T_{VJ} = 25^\circ C; t_p = 10 \mu s$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	≤	450	mA
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$	≤	200	mA
t_{gd}	$T_{VJ} = 25^\circ C; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	≤	2	μs
t_q	$T_{VJ}=125^\circ C; I_T = 20 A, t_p = 200 \mu s; di/dt = -10 A/\mu s$ typ. $V_R = 100 V; dv/dt = 15 V/\mu s; V_D = \frac{2}{3} V_{DRM}$	150		μs
R_{thJC}	per thyristor; sine 180°el	0.6		K/W
	per module	0.1		K/W
R_{thJK}	per thyristor; sine 180°el	0.7		K/W
	per module	0.117		K/W
d_s	Creeping distance on surface	12.7		mm
d_A	Creepage distance in air	9.4		mm
a	Max. allowable acceleration	50		m/s^2

Dimensions in mm (1 mm = 0.0394")



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